**Product data sheet** 

## 1. General description

Planar passivated four quadrant triac in a SOT78 (T0-220AB) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance.

### 2. Features and benefits

- · High blocking voltage capability
- High noise immunity
- · Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

# 3. Applications

- General purpose motor controls
- · General purpose switching

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage		-	-	400	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 91 \text{ °C}$ ; $\overline{Fig. 1}$ ; $\overline{Fig. 2}$ ; $\overline{Fig. 3}$	-	-	25	A
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 20  \text{ms}$ ; $\underline{Fig. 4}$ ; $\underline{Fig. 5}$	-	-	190	Α
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 16.7  ms$	-	-	230	A
T <sub>j</sub>	junction temperature		-	-	125	°C
Static chara	acteristics					
I <sub>GT</sub> gate trigger current	gate trigger current	$V_D$ = 12 V; $I_T$ = 0.1 A; T2+ G+; $T_j$ = 25 °C; Fig. 7	-	6	50	mA
		$V_D$ = 12 V; $I_T$ = 0.1 A; T2+ G-; $T_j$ = 25 °C; Fig. 7	-	10	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$	-	11	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;} $ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$	-	23	75	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>i</sub> = 25 °C; T2+; <u>Fig. 9</u>	-	7	30	mA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; T2-; <u>Fig. 9</u>	-	12	30	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.55	V
Dynamic cha	racteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 268 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	100	300	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 95 ^{\circ}\text{C}; dI_{com}/dt = 9 \text{ A/}$ ms; $I_T = 25 \text{ A}; gate open circuit}$	-	10	-	V/µs

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2	<b>├</b>	G sym051
3	G	gate		Symoon
mb	Т2	mounting base; main terminal 2		
			TO-220AB (SOT78)	

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
MAC223A6	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78		

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# 7. Limiting values

### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	400	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 91 ^{\circ}\text{C}$ ; Fig. 1; Fig. 2; Fig. 3	-	25	Α
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig. 4; Fig. 5	-	190	Α
		full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 16.7 ms	-	230	Α
I <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	180	A²s
dl <sub>T</sub> /dt	rate of rise of on-state	I <sub>G</sub> = 200 mA; T2+ G+	-	50	A/µs
	current	I <sub>G</sub> = 200 mA; T2+ G-	-	50	A/µs
		I <sub>G</sub> = 200 mA; T2- G-	-	50	A/µs
		I <sub>G</sub> = 200 mA; T2- G+	-	10	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
$P_{GM}$	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

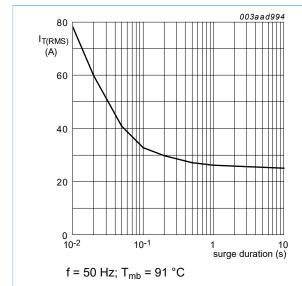


Fig. 1. RMS on-state current as a function of surge duration; maximum values

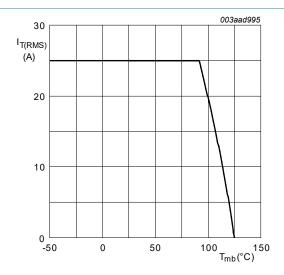


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

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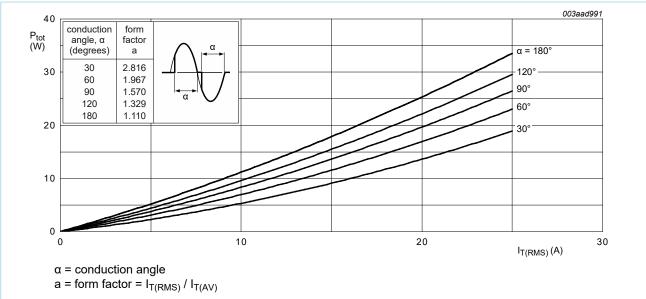


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

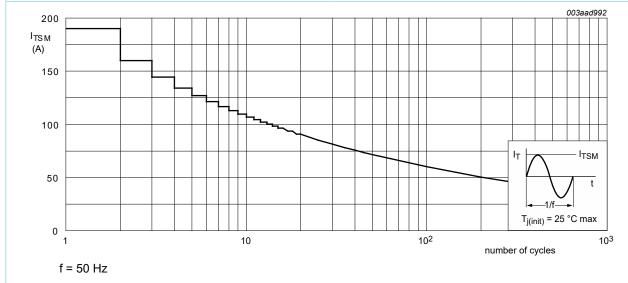
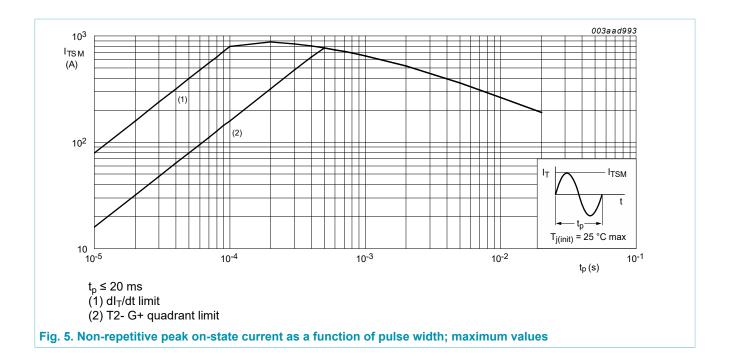


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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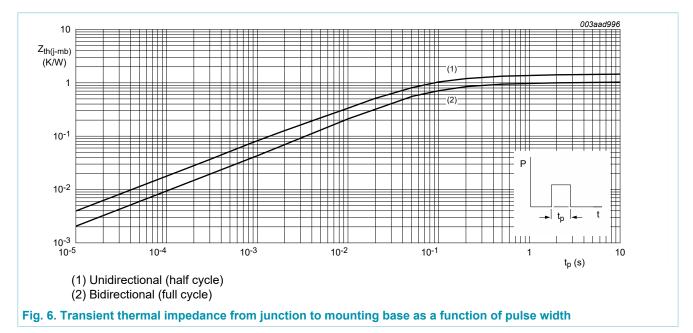
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### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance	full cycle; Fig. 6	-	-	1	K/W
from junction to mounting base		half cycle; Fig. 6	-	-	1.4	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W



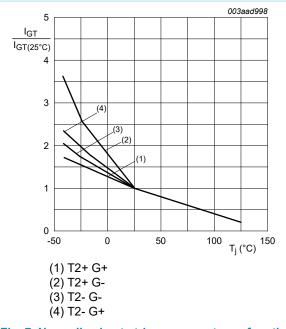
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### 9. Characteristics

#### Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		,	,		
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	6	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	10	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	11	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	23	75	mA
L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	8	40	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	30	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{\text{C}}$	-	18	40	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{\text{C}}$	-	15	60	mA
l <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; T2+; <u>Fig. 9</u>	-	7	30	mA
		V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; T2-; <u>Fig. 9</u>	-	12	30	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.55	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C};$ Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 400 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic ch	naracteristics			'		
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 268 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	100	300	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D$ = 400 V; $T_j$ = 95 °C; $dI_{com}/dt$ = 9 A/ ms; $I_T$ = 25 A; gate open circuit	-	10	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM}$ = 30 A; $V_D$ = 400 V; $I_G$ = 0.1 A; $dI_G/dt$ = 5 A/µs	-	2	-	μs

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003aae000 3  $I_{\mathsf{L}}$ I<sub>L(25°C)</sub> 2 1 0 -50 0 50 100 150 T<sub>i</sub> (°C)

Fig. 8. Normalized latching current as a function of junction temperature

Fig. 7. Normalized gate trigger current as a function of junction temperature

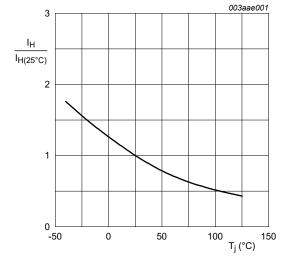
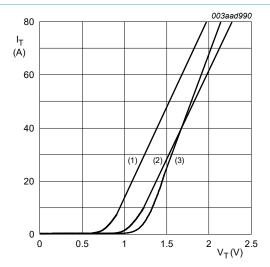


Fig. 9. Normalized holding current as a function of junction temperature



 $V_o$  = 1.073 V;  $R_s$  = 0.015 Ω (1)  $T_j$  = 125 °C; typical values (2)  $T_j$  = 125 °C; maximum values (3)  $T_j$  = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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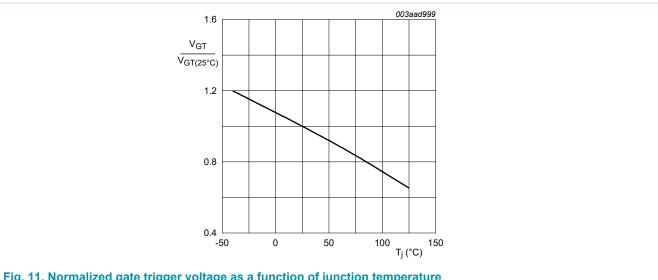
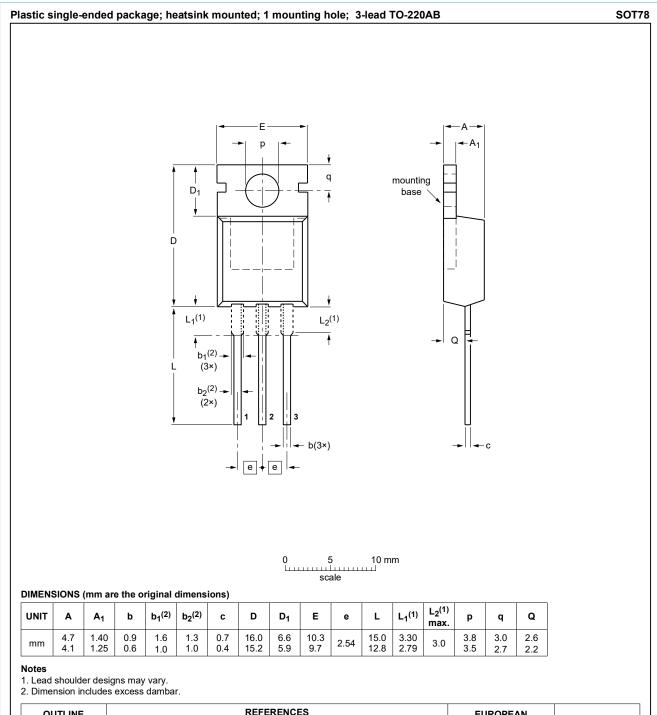


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

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# 10. Package outline



OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		<del>08-04-23</del> 08-06-13

Fig. 12. Package outline TO-220AB (SOT78)

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#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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